

60 V, 4.2 A PNP low VCEsat transistor

9 November 2023

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS304NX

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- + High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- High collector current gain (hFE) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

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- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

4. Quick reference data

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
Ic	collector current		-	-	-4.2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-8.4	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	48	69	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base		B
			SOT89	sym132

6. Ordering information

Table 3. Ordering information						
Type number	Package	age				
	Name	Description	Version			
PBSS304PX		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>			

7. Marking

Table 4. Marking codes	
Type number	Marking code[1]
PBSS304PX	%5L

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

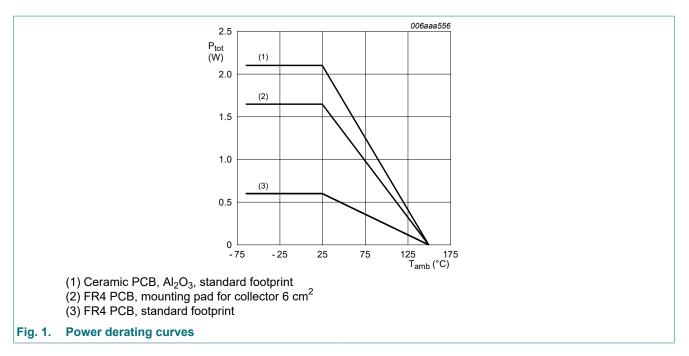
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-4.2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-8.4	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

60 V, 4.2 A PNP low VCEsat transistor



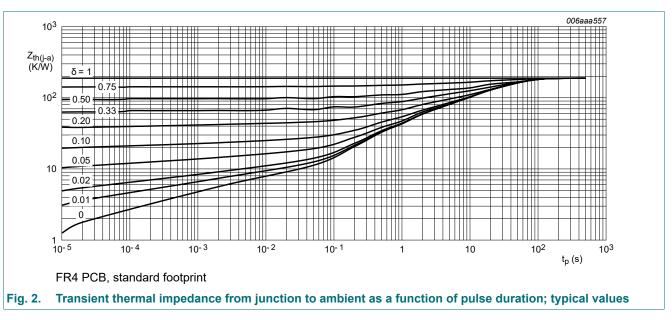
9. Thermal characteristics

Table 6. Thermal characteristics Parameter Conditions Min Unit Symbol Max Тур 208 K/W thermal resistance from in free air [1] R_{th(j-a)} junction to ambient K/W [2] 76 K/W [3] 60 $R_{th(j-sp)}$ thermal resistance from 20 K/W junction to solder point

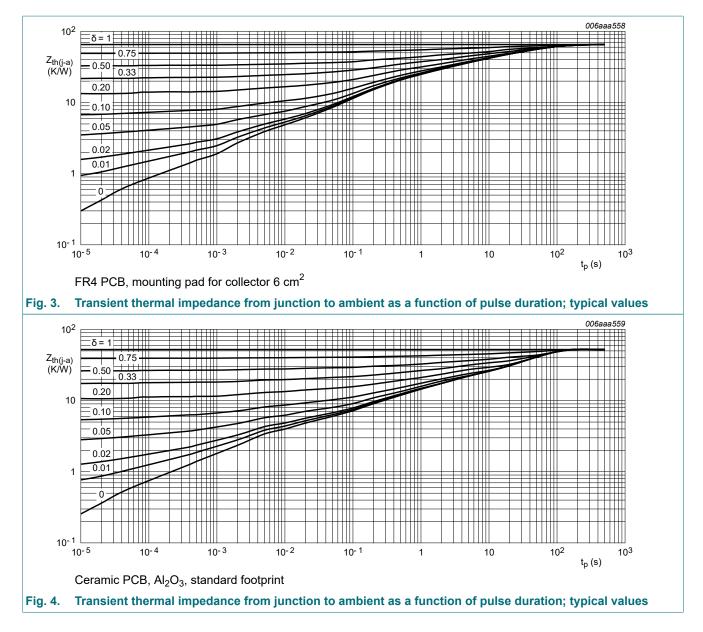
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.



60 V, 4.2 A PNP low VCEsat transistor



10. Characteristics

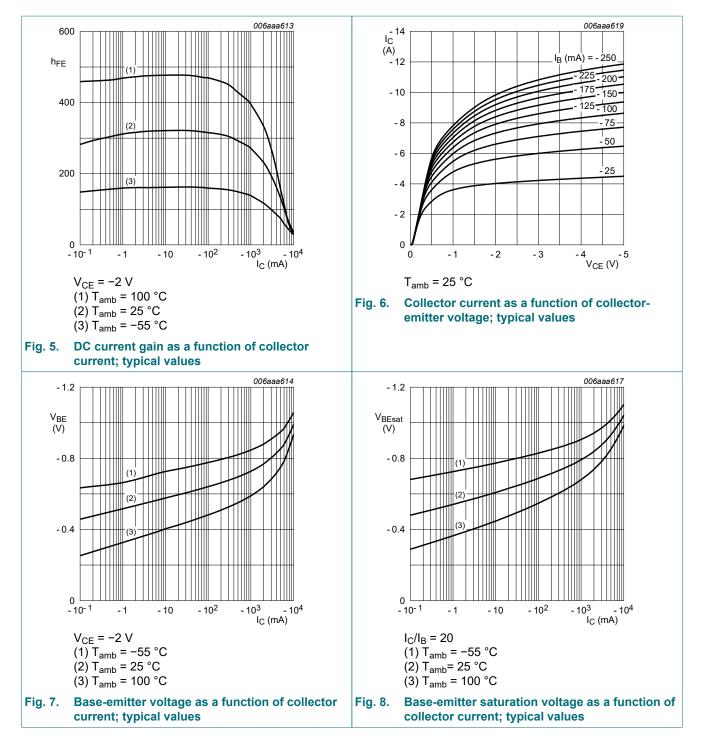
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off current	V_{CB} = -60 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
		V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-100	nA

60 V, 4.2 A PNP low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -0.5 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	295	-	
		V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	270	-	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	150	230	-	
		V_{CE} = -2 V; I _C = -4 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	120	170	-	
		V_{CE} = -2 V; I _C = -6 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	60	100	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-35	-50	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-65	-90	mV
		I_{C} = -1 A; I_{B} = -10 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-130	-190	mV
		I_{C} = -2 A; I_{B} = -40 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-155	-220	mV
		I_{C} = -4 A; I_{B} = -200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-195	-275	mV
		I_{C} = -4 A; I_{B} = -400 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-150	-210	mV
		I_{C} = -4.2 A; I_{B} = -210 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-220	-310	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	78	110	mΩ
		I_{C} = -4 A; I_{B} = -200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	48	69	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-0.81	-0.9	V
		I_{C} = -4 A; I_{B} = -400 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1.05	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-0.77	-0.85	V
d	delay time	V _{CC} = -12.5 V; I _C = -3 A; I _{Bon} = -0.15 A;	-	15	-	ns
r	rise time	I _{Boff} = 0.15 A; T _{amb} = 25 °C	-	65	-	ns
on	turn-on time		-	80	-	ns
·S	storage time		-	225	-	ns
f	fall time		-	95	-	ns
t _{off}	turn-off time		-	320	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	90	120	pF

60 V, 4.2 A PNP low VCEsat transistor

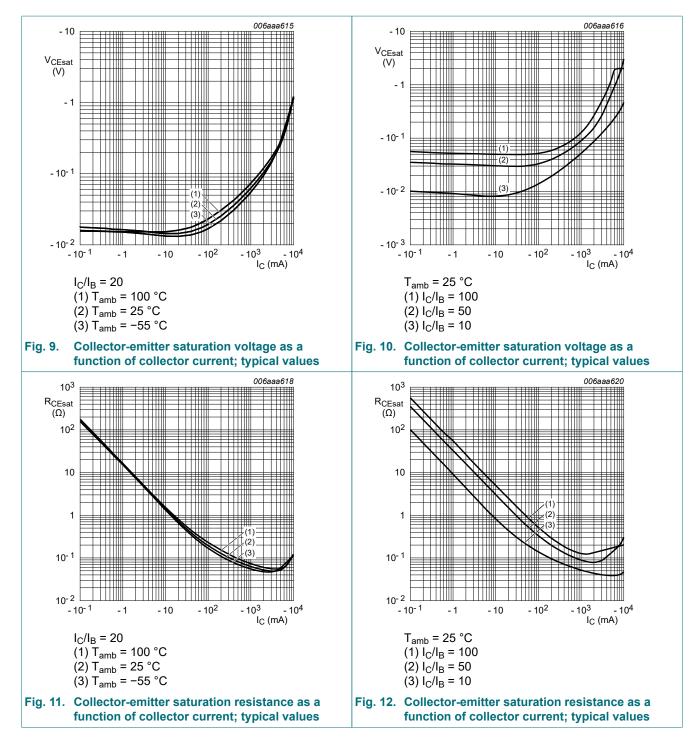


PBSS304PX

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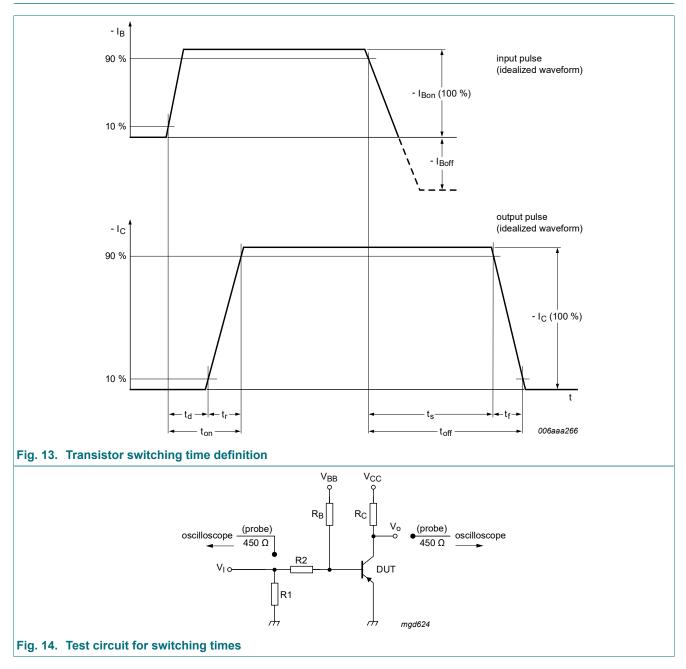
6 / 13

60 V, 4.2 A PNP low VCEsat transistor



60 V, 4.2 A PNP low VCEsat transistor

11. Test information

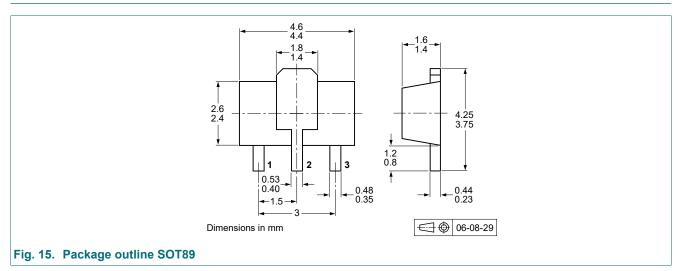


Quality information

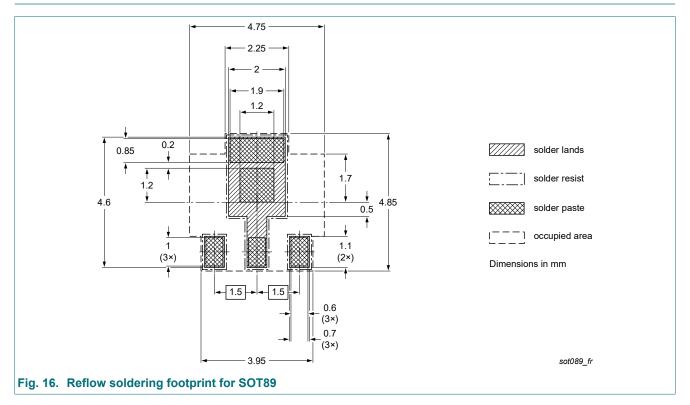
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 4.2 A PNP low VCEsat transistor

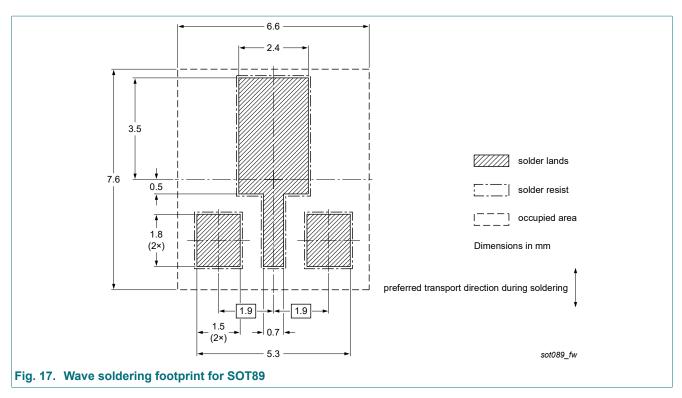
12. Package outline



13. Soldering



60 V, 4.2 A PNP low VCEsat transistor



14. Revision history

Table 8. Revision hi	story						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS304PX v.3	20231109	Product data sheet	-	PBSS304PX_2			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. Section "Mounting" removed. 						
PBSS304PX_2	20091208	Product data sheet	-	PBSS304PX_1			
PBSS304PX_1	20060816	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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60 V, 4.2 A PNP low VCEsat transistor

Contents

1.	General description	.1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	.1
5.	Pinning information	.2
6.	Ordering information	.2
7.	Marking	.2
8.	Limiting values	2
9.	Thermal characteristics	3
10.	Characteristics	4
11.	Test information	. 8
12.	Package outline	9
13.	Soldering	9
14.	Revision history1	1
	Legal information1	

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